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PROCESS FOR MODIFIED OXIDATION OF A SEMICONDUCTOR SUBSTRATE USING CHLORINE PLASMA

ABSTRACT

A process for thermal oxidation of a semiconductor substrate comprising exposing the substrate to a chlorine plasma, and then heating the substrate in an oxidizing ambient. The substrate may comprise silicon, germanium, or a combination thereof. The heating step may further comprise heating at a temperature of between about 750°C and about 850°C.

Fig. 5